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Stocking Distributor

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Rohm Semiconductor RSQ035N03TR

For any questions, you can email us directly: sales@integrated-circuit.com

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RSQ035N03

Transistors

4V Drive Nch MOS FET RSQ035N03

Structure

Silicon N-channel MOS FET

Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TSMT6).

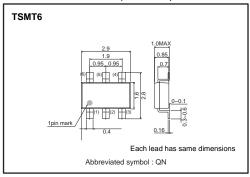
Applications

Switching

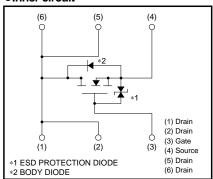
Packaging specifications

	Package	Taping	
Type	Code	TR	
	Basic ordering unit (pieces)	3000	
RSQ035N0	0		

External dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	30	V
Gate-source voltage		Vgss	20	V
Drain current	Continuous	lσ	±3.5	Α
Drain current	Pulsed	IDP *1	±14	Α
Source current	Continuous	Is	1.0	А
(Body diode)	Pulsed	Isp *1	14	Α
Total power dissipation		P _D *2	1.25	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

^{*1} Pw≤10μs, Duty cycle≤1% *2 Mounted on a ceramic board

*2 Mounted on a ceramic board

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	100	°C/W

^{*} Mounted on a ceramic board







RSQ035N03

Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	-	10	μΑ	V _{GS} =20V, V _{DS} =0V
Drain-source breakdown voltage	V _(BR) DSS	30	-	_	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	-	-	1	μΑ	V _{DS} = 30V, V _{GS} =0V
Gate threshold voltage	VGS (th)	1.0	-	2.5	V	VDS= 10V, ID= 1mA
Static drain-source on-state resistance		-	44	62	mΩ	I _D = 3.5A, V _{GS} = 10V
	R _{DS (on)} *	-	60	84	mΩ	I _D = 3.5A, V _{GS} = 4.5V
		-	67	94	mΩ	I _D = 3.5A, V _{GS} = 4V
Forward transfer admittance	Y _{fs} *	2.0	-	_	S	V _{DS} = 10V, I _D = 3.5A
Input capacitance	Ciss	_	290	_	pF	V _{DS} = 10V
Output capacitance	Coss	_	85	_	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	-	55	_	pF	f=1MHz
Turn-on delay time	td (on) *	-	7	-	ns	V _{DD} ≒ 15V
Rise time	tr *	-	9	-	ns	I _D = 1.75A V _G s= 10V
Turn-off delay time	t _{d (off)} *	-	24	_	ns	$R_{L}=8.57\Omega$
Fall time	t _f *	-	6	_	ns	R _G =10Ω
Total gate charge	Qg *	-	5.3	7.4	nC	V _{DD} ≒15V V _{GS} =5V
Gate-source charge	Qgs *	_	1.0	_	nC] I _D = 3.5A
Gate-drain charge	Q _{gd} *	_	1.4	_	nC	$R_L=4.29\Omega$ $R_G=10\Omega$

^{*}Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	VsD	_	_	1.2	V	I _S = 1.0A, V _{GS} =0V



Distributor of Rohm Semiconductor: Excellent Integrated System Limited

Datasheet of RSQ035N03TR - MOSFET N-CH 30V 3.5A TSMT6

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Appendix

Notes

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